

## N - CHANNEL ENHANCEMENT MODE " SINGLE FEATURE SIZE™ " POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB60NE06-1	60 V	< 0.016 Ω	60 A

- TYPICAL R<sub>DS(on)</sub> = 0.013 Ω
- EXCEPTIONAL dV/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW GATE CHARGE 100 °C
- HIGH dV/dt CAPABILITY
- APPLICATION ORIENTED CHARACTERIZATION
- FOR THROUGH-HOLE VERSION CONTACT SALES OFFICE

### DESCRIPTION

This Power Mosfet is the latest development of SGS-THOMSON unique " Single Feature Size™ " strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### APPLICATIONS

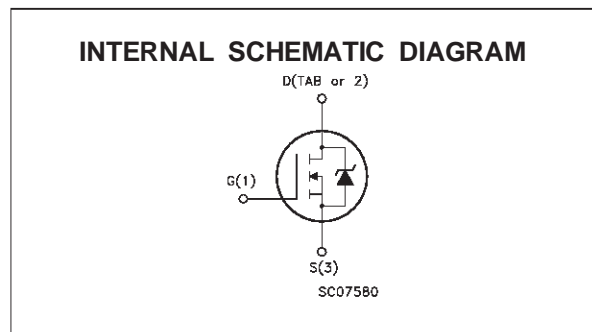
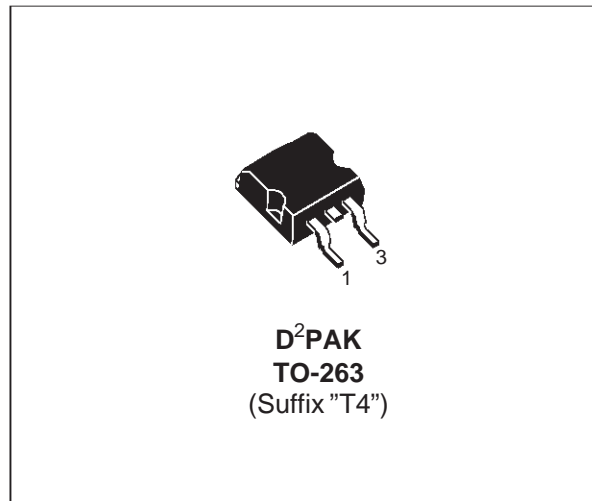
- DC MOTOR CONTROL
- DC-DC & DC-AC CONVERTERS
- SYNCHRONOUS RECTIFICATION

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60	V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	60	V
V <sub>GS</sub>	Gate-source Voltage	± 20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	60	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	42	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	240	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	150	W
	Derating Factor	1	W/°C
dV/dt(1)	Peak Diode Recovery voltage slope	6	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 60 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ T<sub>JMAX</sub>



## STB60NE06-16

### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1 °C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5 °C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ	0.5 °C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300 °C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	60	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)	350	mJ

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>c</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			± 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 30 A		0.013	0.016	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	60			A

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 30 A	20	35		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		4600	6200	pF
C <sub>oss</sub>	Output Capacitance			580	800	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			140	200	pF

**ELECTRICAL CHARACTERISTICS** (continued)

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 30\text{ V}$ $I_D = 30\text{ A}$		40	60	ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		125	180	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 48\text{ V}$ $I_D = 60\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$		280		A/ $\mu$ s
$Q_g$	Total Gate Charge	$V_{DD} = 48\text{ V}$ $I_D = 60\text{ A}$ $V_{GS} = 10\text{ V}$		115	160	nC
$Q_{gs}$	Gate-Source Charge			25		nC
$Q_{gd}$	Gate-Drain Charge			40		nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(off)}$	Off-voltage Rise Time	$V_{DD} = 48\text{ V}$ $I_D = 60\text{ A}$		15	25	ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		150	210	ns
$t_c$	Cross-over Time			180	260	ns

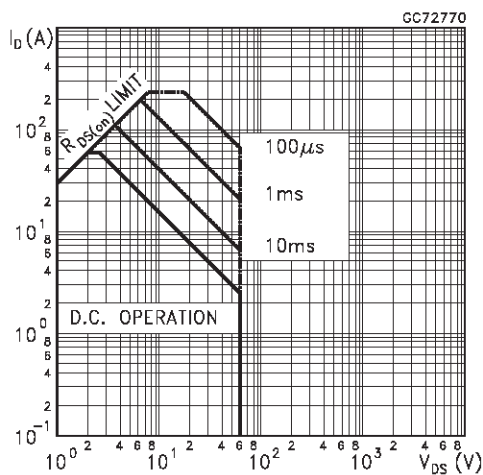
**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				60	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				240	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 60\text{ A}$ $V_{GS} = 0$			1.5	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 60\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		100		ns
$Q_{rr}$	Reverse Recovery Charge			0.4		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			8		A

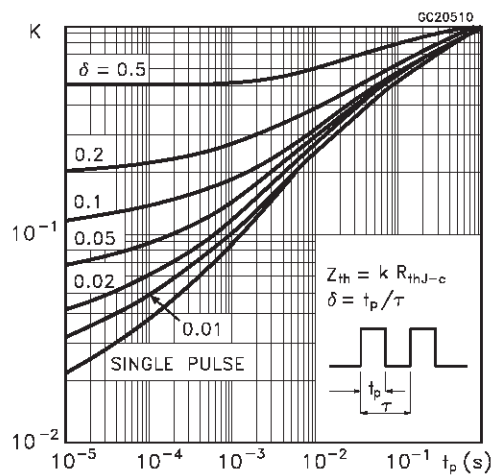
(\*) Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5 %

( $\bullet$ ) Pulse width limited by safe operating area

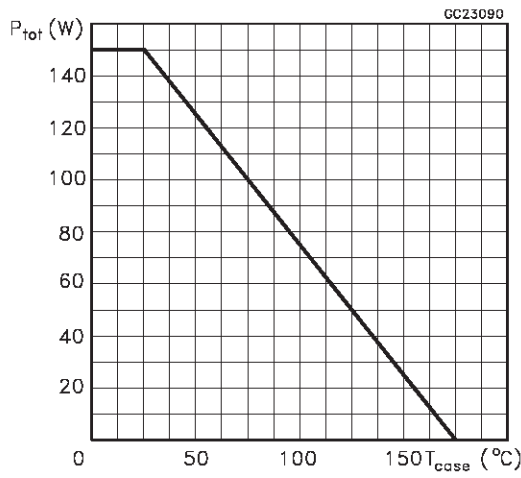
**Safe Operating Area**



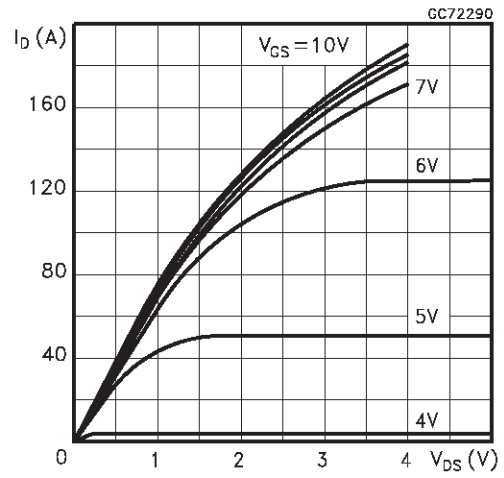
**Thermal Impedance**



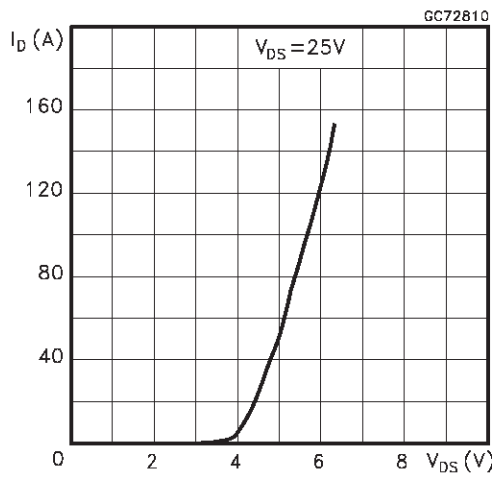
Derating Curve



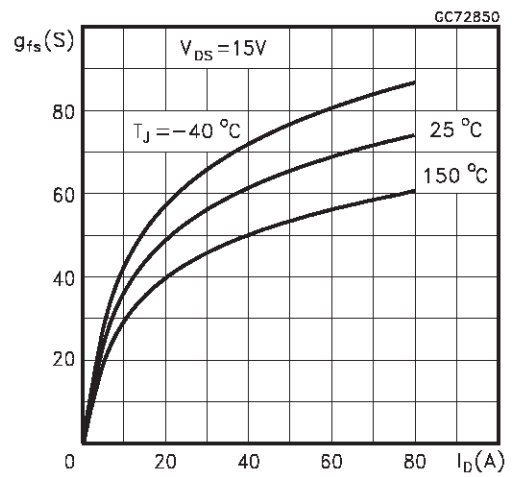
Output Characteristics



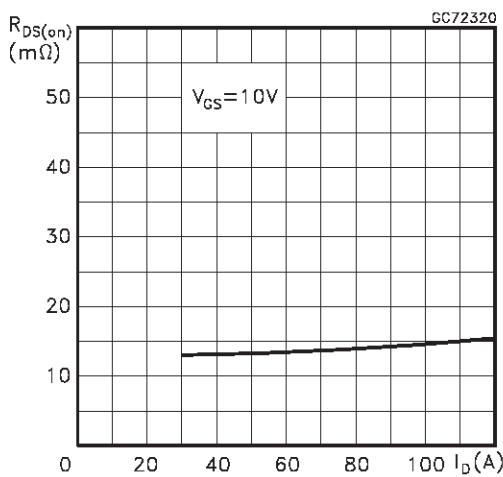
Transfer Characteristics



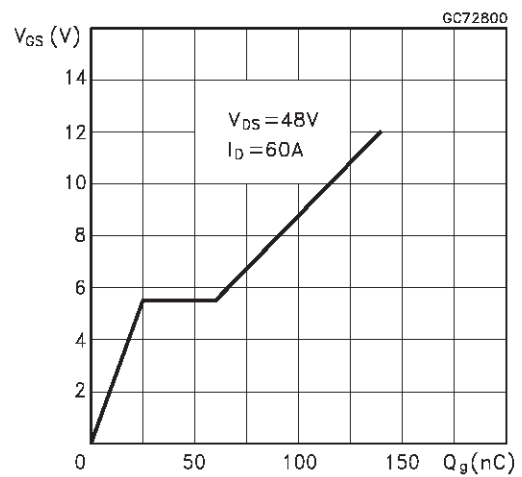
Transconductance



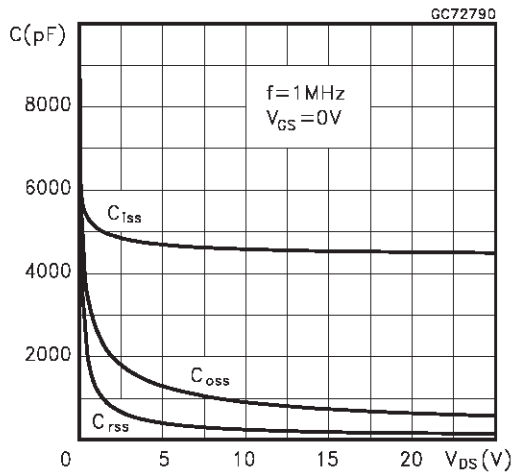
Static Drain-source On Resistance



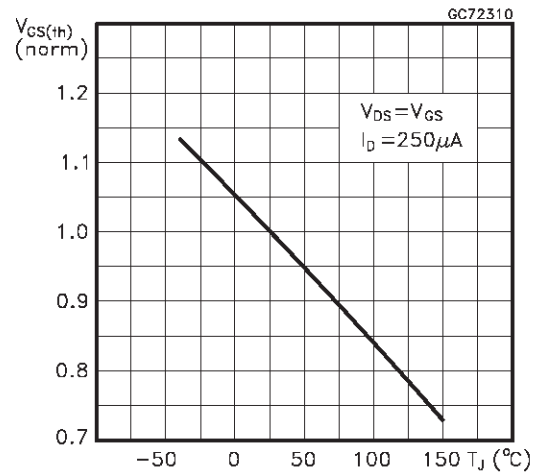
Gate Charge vs Gate-source Voltage



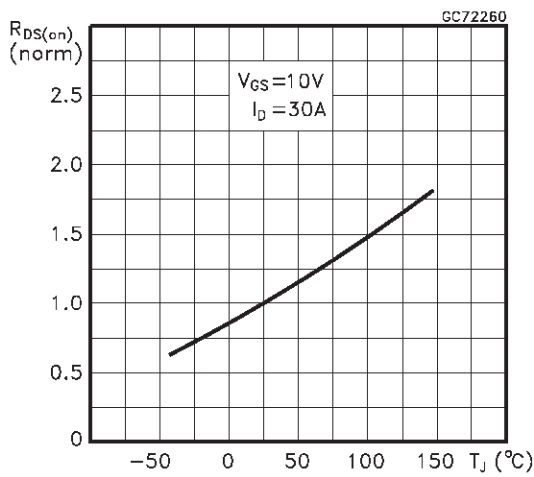
Capacitance Variations



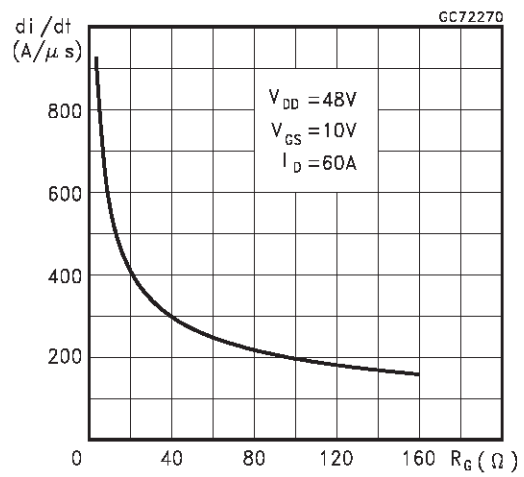
Normalized Gate Threshold Voltage vs Temperature



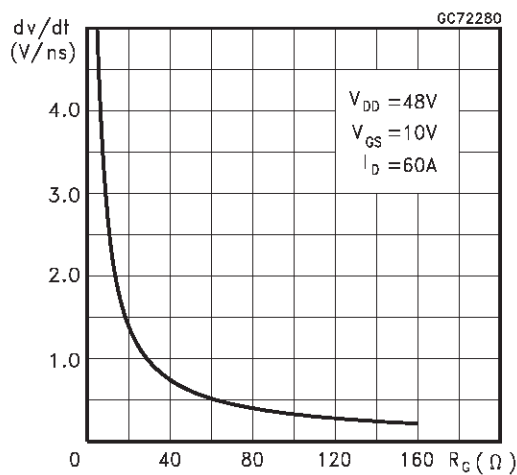
Normalized On Resistance vs Temperature



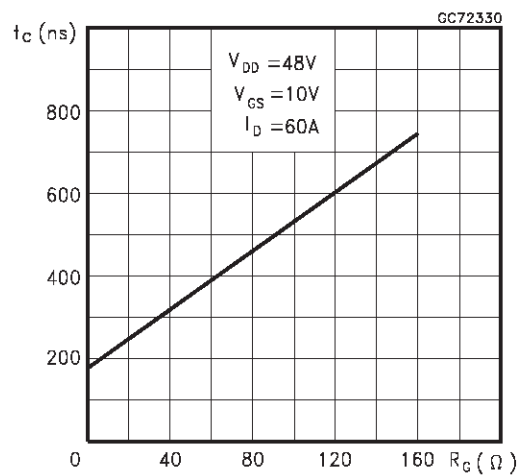
Turn-on Current Slope



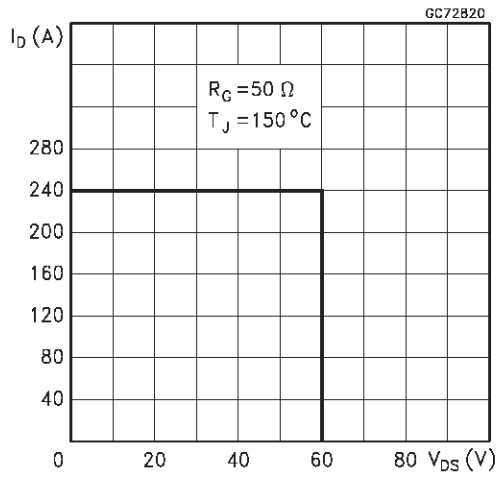
Turn-off Drain-source Voltage Slope



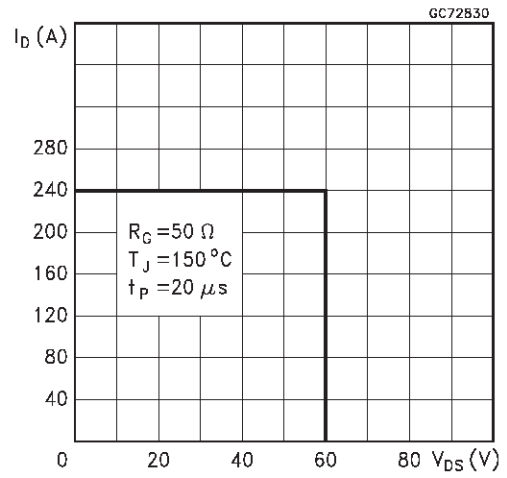
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

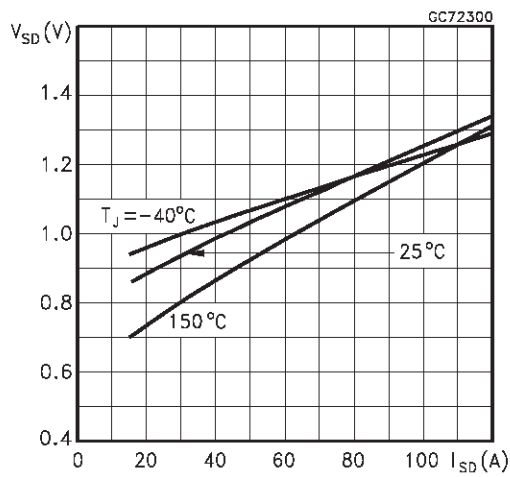


Fig. 1: Unclamped Inductive Load Test Circuit

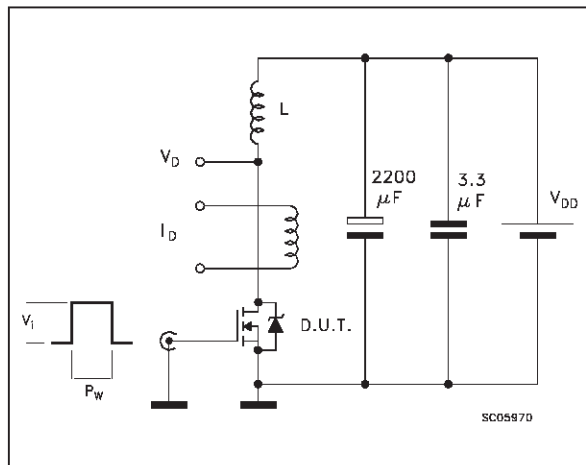
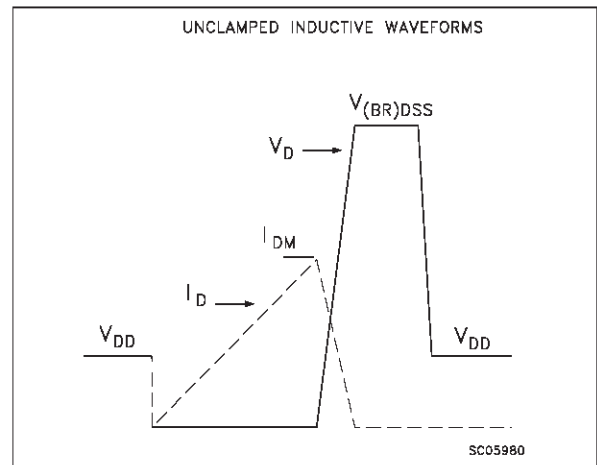
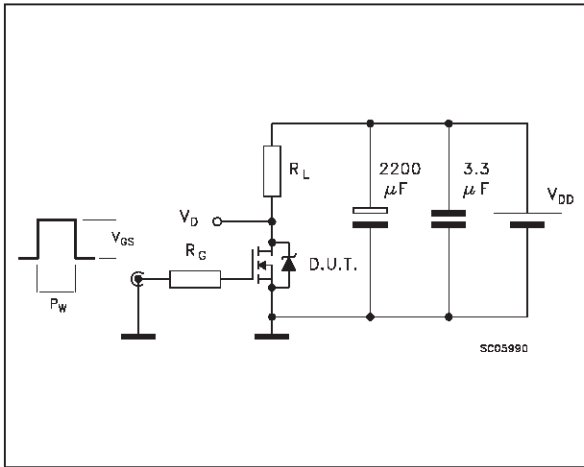


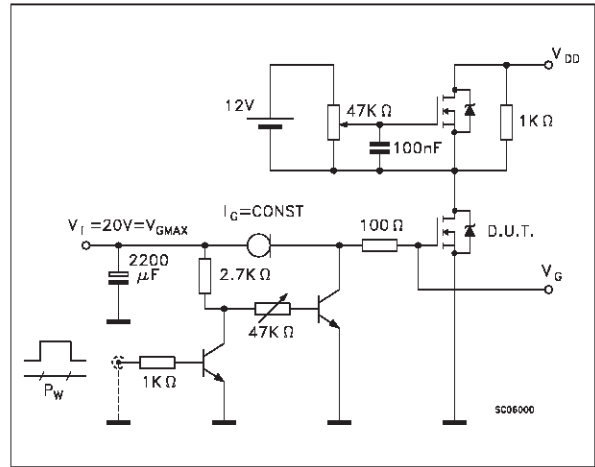
Fig. 2: Unclamped Inductive Waveform



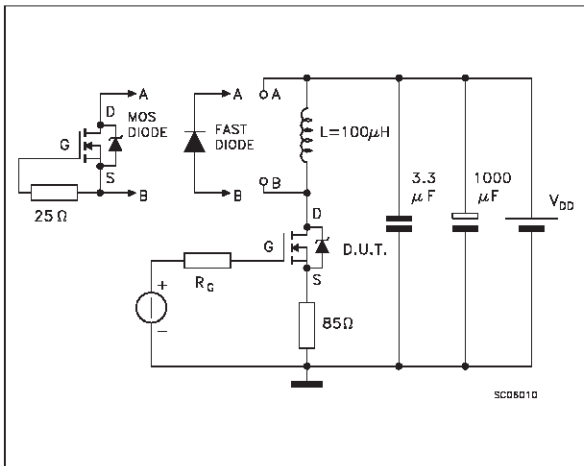
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

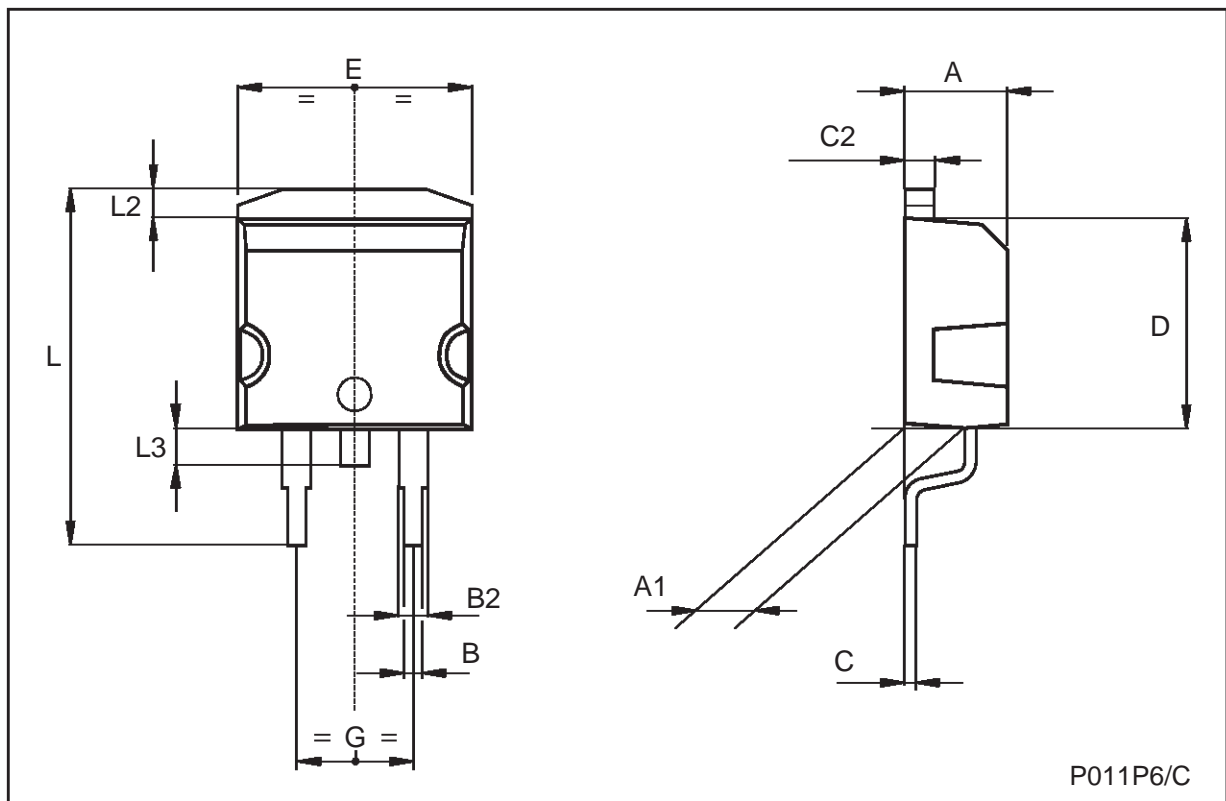


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



**TO-263 (D<sup>2</sup>PAK) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.25		1.4	0.049		0.055
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	8.95		9.35	0.352		0.368
E	10		10.28	0.393		0.404
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068





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